

優恩半導體 UN Semiconductor[®]



Transient Voltage Suppressors for ESD Protection

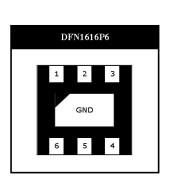
ULC0506P6

Description

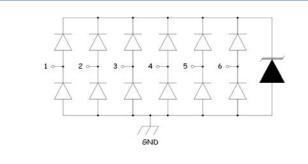
The ULC0506P6 is ultra low capacitance TVS arrays designed to protect high speed data interfaces. This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from over-voltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

Feature

- 100 Watts Peak Pulse Power per Line (tp=8/20µs)
- Protects Six High Speed Lines
- Low Clamping Voltage
- Working Voltages : 5V
- Low Leakage Current
- ♦ IEC61000-4-2(ESD): ±15kV (air), ±8kV (contact);
- IEC61000-4-4 (EFT) 40A (5/50 η s)
- IEC61000-4-5 (LIGHTING) 4A (8/20 μ s)



Functional Diagram



Applications

- USB 3.0 / USB 3.1 Interfaces
- HDMI 1.4 / HDMI 2.0 Interfaces
- High Speed I/O Lines
- Video Graphics Cards
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Industrial Controls
- Peripherals

Weight 4.2 Millgrams (Approximate)

• Quantity Per Reel : 3,000pcs

DFN1616P6 Package (1.6x1.6x0.5mm)

Molding Compound Flammability Rating : UL 94V-O

Reel Size : 7 inch

Mechanical Data

- Lead Finish : Lead Free
- Device Marking: UC56

Mechanical Characteristics

Symbol	Parameter	Value	Units
Ррр	Peak Pulse Power (tp=8/20µs waveform)	100	Watts
TJ	Operating Junction Temperature Range	-40to +125	°C
Т _{stg}	Storage Temperature Range	-55 to +150	°C
T∟	Soldering Temperature, T max = 10s	260	°C

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Electrical Characteristics (@ 25 $^{\circ}$ Unless Otherwise Specified)						
Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Reverse Working Voltage	V _{RWM}				5	V
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	6			V
Reverse Leakage Current	I _R	V _{RWM} =5V ; T=25°C			1	μA
Junction capacitance	CJ	V _R =0V , f=1MHz ;		0.4		pF
Positive Clamping		I _{PP} =1A,T _P =8/20µS;			12	
Voltage	Vc	I _{PP} =4A,T _P =8/20µS;			25	V

Characteristic Curves

Fig1. Insection Loss (S21)

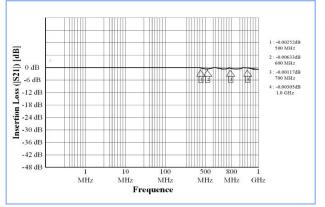


Fig3. Clamping Voltage vs. Peak Pulse Current (tp=8/20us)

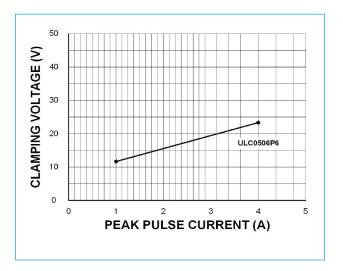


Fig2. Power Derating Curve

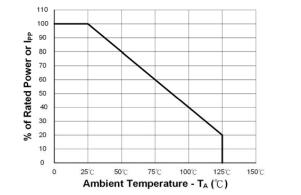
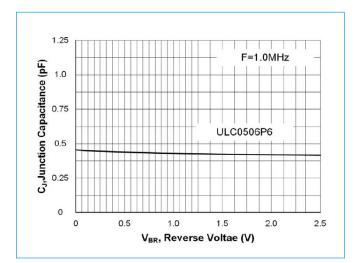


Fig4. Typic Capacitance vs. Reverse Voltage



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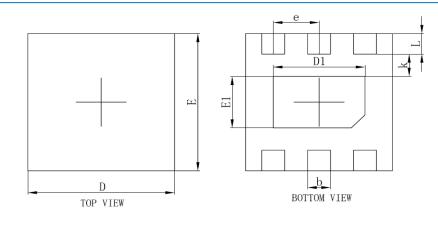


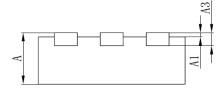


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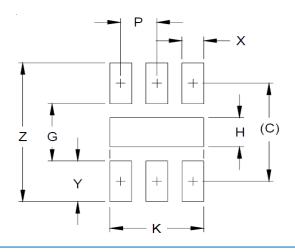
DFN1616P6 Package Outline & Dimensions





Sumphiel	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.450/0.550	0.550/0.650	0.018/0.022	0.022/0.026	
A1	0.000	0.050	0.000	0.002	
A3	0.152REF.		0.006REF.		
D	1.550	1.650	0.061	0.065	
E	1.550	1.650	0.061	0.065	
E1	0.500	0.700	0.020	0.028	
D1	0.900	1.100	0.035	0.043	
k	0.200MIN.		0.008REF.		
b	0.200	0.300	0.008	0.012	
е	0.500BSC.		0.020BSC.		
Ĺ	0.164	0.316	0.006	0.012	

*** SOLDERING FOOTPRINT**



	DIMENSIONS		
DIM	INCHES	MILLIMETERS	
С	.060	1.52	
G	.035	0.89	
Н	.018	0.45	
K	.051	1.30	
Р	.020	0.50	
X	.012	0.30	
Y	.025	0.63	
Z	.085	2.15	

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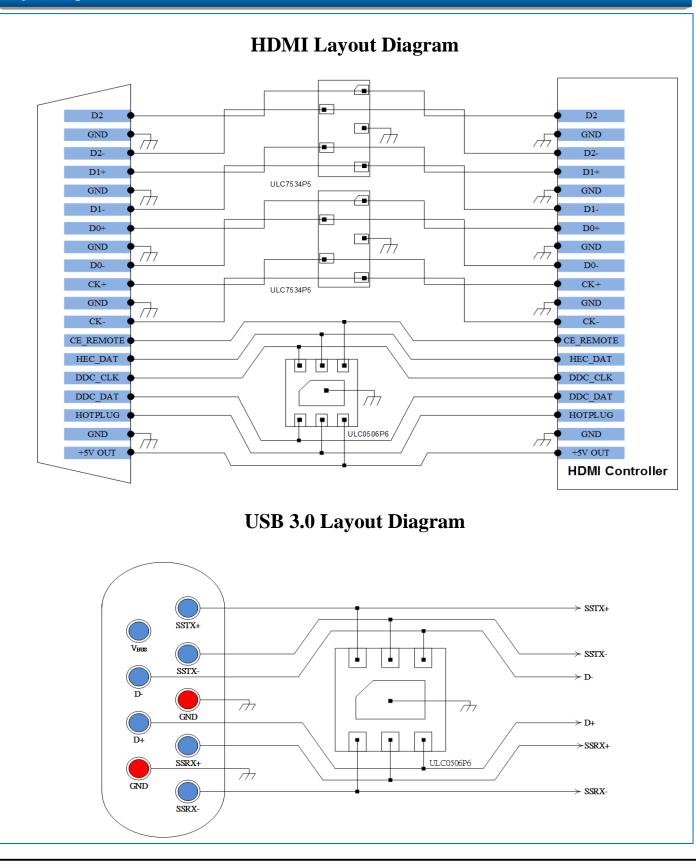




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Layout Diagrams



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